(19) World Intellectual Property Organization International Bureau





(43) International Publication Date 18 December 2003 (18.12.2003)

PCT

(10) International Publication Number WO 03/105341 A1

(51) International Patent Classification⁷: H03F 3/60, G01R 31/02

H03H 11/46,

(21) International Application Number: PCT/SE02/01092

(22) International Filing Date: 6 June 2002 (06.06.2002)

(25) Filing Language:

English

(26) Publication Language:

English

(71) Applicant (for all designated States except US): TELE-FONAKTIEBOLAGET LM ERICSSON (PUBL) [SE/SE]; S-126 25 Stockholm (SE).

(72) Inventor; and

(75) Inventor/Applicant (for US only): BLADH, Mats [SE/SE]; Önnemovägen 116, S-146 53 Tullinge (SE).

(74) Agent: ERICSSON AB; Patent Unit Service and Backbone Networks, S-126 25 Stockholm (SE).

(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZM, ZW.

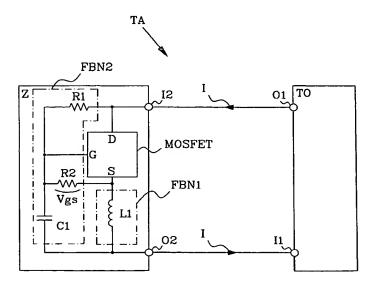
(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: ACTIVE LOAD ARRANGEMENT



(57) Abstract: The present invention relates to an active load arrangement Z used to provide proper output load to an object TO under test. The arrangement Z comprises a voltage controlled transistor MOSFET having a source S, a gate G and a drain D. The drain D is associated with the gate G and connected to an arrangement input I2 associated with an output 01 of the object under test. The source S is connected to an arrangement output 02 associated with an input I1 of the object under test. A feedback arrangement is connected to the source S and the gate G. The feedback arrangement changes phase and amplitude of the gate-to-source voltage by varying frequency in order to obtain low impedance at low impedance at low frequencies and high impedance at high frequencies.



03/105341 A1